

SANYO Semiconductors

DATA SHEET



Monolithic Linear IC For Car Stereo 2-Channel Preamplifier

Features

- On-chip 2 preamplifiers
- Good ripple rejection owing to on-chip voltage regulator
- Minimum number of external parts required
- Low noise
- 8-pin SIP package facilitating easy mounting
- Pin-compatible with LA3160

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum Supply Voltage	V _{CC} max		18	V
Allowable Power Dissipation	Pd max		200	mW
Operating Temperature	Topr		-20 to +75	°C
Storage Temperature	Tstg		-40 to +125	°C

Recommended Operating Conditions at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Supply Voltage	Vcc		9	V
Load Resistance	PL		10k	Ω

Any and all ANYO Semiconductor Co.,Ltd. products described or contained herein are, with regard to "standard applic ion" intended for the use as general electronics equipment (home appliances, AV equipment, communication device, office equipment, industrial equipment etc.). The products mentioned herein shall not be intended in use or any "special application" (medical equipment whose purpose is to sustain life, aerospace instruction, number of device, burning appliances, transportation machine, traffic signal system, safety end ment. tc.) that shall require extremely high level of reliability and can directly threaten human lives in case failure or malfunction of the product or may cause harm to human bodies, nor shall they grant any guarantee use of, you should intend to use our products for applications outside the standard applications of our custo. who is considering such use and/or outside the scope of our intended standard applications, please consult with us prior to the intended use. If there is no consultation or inquiry before the intended use, our customer shall be solely responsible for the use.

Specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

SANYO Semiconductor Co., Ltd. TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

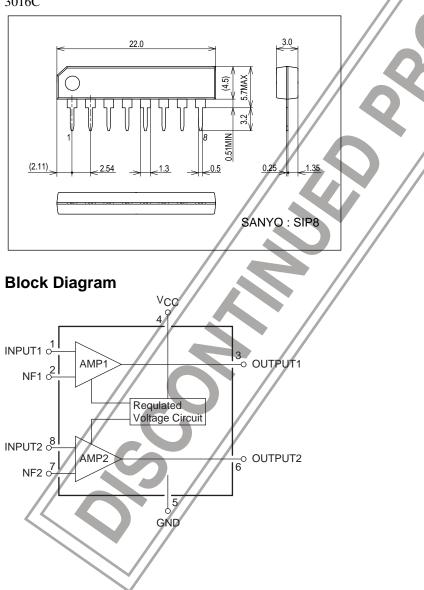
Electrical Characteristics at Ta = 25°C, V_{CC} = 9V, R_L = 10k Ω , Rg = 600 Ω , f = 1kHz, NAB

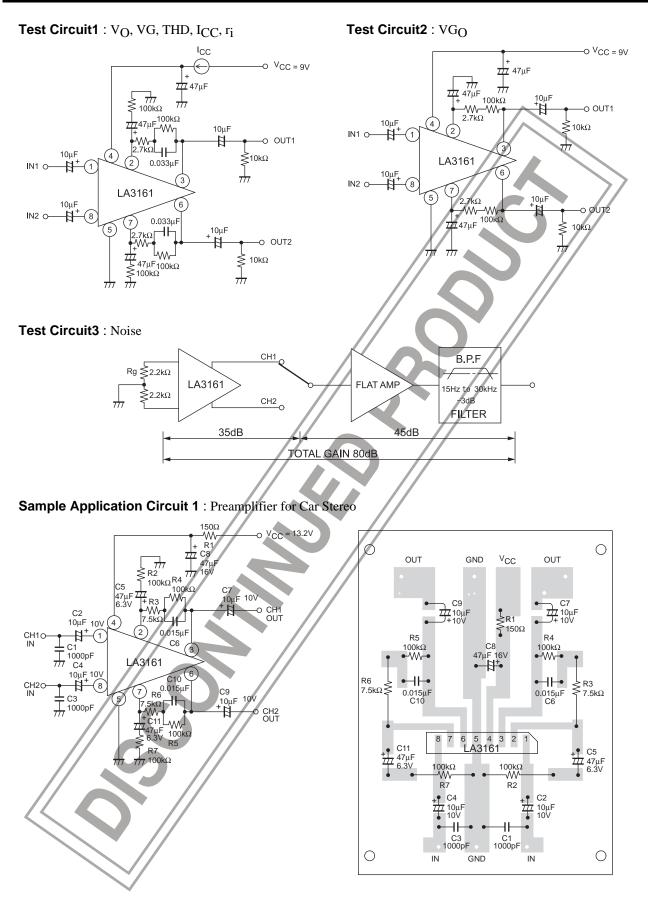
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol Conditions		min	typ	max	Onit	
Current Dissipation	Icc			6.5	8.0	mA	
Voltage Gain	VG	Closed loop		35		dB	
		Open loop, V _O = 0.77V	70	78		dB	
Output Voltage	VO	THD = 1%	1.0	1.3		V	
Total Hamonic Distortion	THD	V _O = 0.5V		0.05	0.30	%	
Input Resistance	rj		70k	100k	/	Ω	
Equivalent Input Noise Voltage	V _{NI}	$Rg = 2.2k\Omega$		1.2	2.0	µF	
Crosstalk	СТ	$Rg = 2.2k\Omega$	-50	-65		dB	
Ripple Rejection	Rr			-40		dB	

Package Dimensions

unit : mm (typ)

3016C





Function of External Parts

C₂, C₄ are input coupling capacitors. In NAB equalizer amplifier, the gain at low frequencies is high and 1/f noise inside the IC is emphasized as output noise. Therefore, if the reactance of capacitor at low frequencies is increased, the dependence of 1/f noise on the signal source resistance causes the output noise voltage to deteriorate, and the value of reactance must be made small enough as compared with the signal source resistance. C₂, C₄ also influence the operation start time and the adequate value of these capacitors is 10μ F. (Since C₂, C₄ of less than 4.7 μ F make the operation start time longer, use C₂, C₄, of 4.7 μ F or more).

C5, C11 are NF capacitors. The lower cut-off frequency depends on the value of these capacitors

If the lower cut-off frequency is taken as f_L :

C5 (C11) = $1/2\pi \cdot f_L \cdot R2$ (R7)

If the value of this capacitor is made larger, the operation start time of amplifier is more delayed. The adequate value of capacitor is 47μ F.

The frequency characteristic of the equalizer amplifier depends on C_6 and R_4 , R_3 (C_{10} and R_5 , R_6). The time constants to obtain the standard NAB characteristic are as shown below.

Tape speed	9.5cm/s	4.75cm/s
C6 (R3 + R4)	3180µs	1590µs
R3 C6	90µs	120µs

C8 is bias capacitor for the power line. C8 of 47μ F is inserted at a point as close to the power supply pin (pin 4) as possible.

C₁, C₃ are for preventing radio interference in the strong electric field, interference attributable to engine noise, and blocking oscillation at the time of large amplitude operation. The adequate value of C₁, C₃ is approximately 1000pF. C₇, C₉ are output coupling capacitors. The adequate value of C₇, C₉ is 10μ F.

NAB element and determination of gain

Since the DC feedback is provided by R_1 , R_2 of NAB element, which brings about DC output potential at pins 3, 6, it is impossible to change the value of R_1 , R_2 of NAB element greatly. Therefore, when determining the gain, change R_{NF} with R_1 , R_2 , C_1 (NAB element) kept constant.

Pin 2 or Pin 8
$$\leftarrow$$
 R2
 \downarrow^+ \downarrow^+ $\downarrow^ \downarrow^ \downarrow^-$

(1) How to obtain R_{NF}

Impedance Z of NAB element is

$$Z = \frac{1}{1/R1 + j\omega C1} + R2$$

= (R1 + R2) { 1 + j\omega C1{R1 R2/(R1 + R2)}
1 + j\omega C1R1

For a general negative feedback amplifier circuit, $A = Ao/(1 + Ao\beta)$ applies, and $Z = A \cdot R_{NF}$ is obtained under conditions of Ao>>A, A>>1 ($\beta = R_{NF}/(R_{NF} + Z)$, Ao = open-loop gain, A = feedback gain). Therefore, we can use an approximation of $R_{NF} = Z/A$.

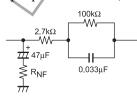
A = (VG for 1kHz) times, (Set R₁, R₂ at approximately $100k\Omega$)

Each time constant of NAB characteristic.

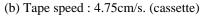
Tape speed	9.5cm/s	4.75cm/s
T1 C1, R1	3180µs	1590µs
T2 C1 (R1//R2)	90µs	120µs

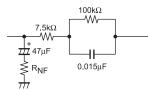
(2) Examples of NAB Constants

(a) Tape speed : 9.5cm/s. (8 tracks)



VG	30	35	40	dB
R _{NF}	180	100	56	Ω





VG : RNF

VG	30	35	40	dB	
R _{NF}	440	240	130	Ω	

(c) Flat amplifier



VG : R _N	F				
VG	30	35	40	dB	
R _{NF}	3.2	1.8	1	kΩ	1/

Proper cares in using IC

1. Maximum Rating

If the IC is used in the vicinity of the maximum rating, even a slight variation in conditions may cause the maximum rating to be exceeded, thereby leading to a breakdown. Allow an ample margin of variation for supply voltage, etc. and use the IC in the range where the maximum rating is not exceed.

2. Short between pins

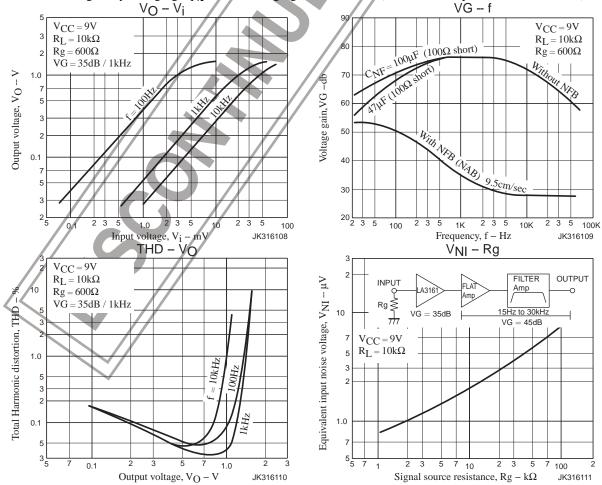
If the supply voltage is applied when the space between pins is shorted, a breakdown or deterioration may occur. When installing the IC on the board or applying the supply voltage, make sure that the space between pins is not shorted with solder, etc.

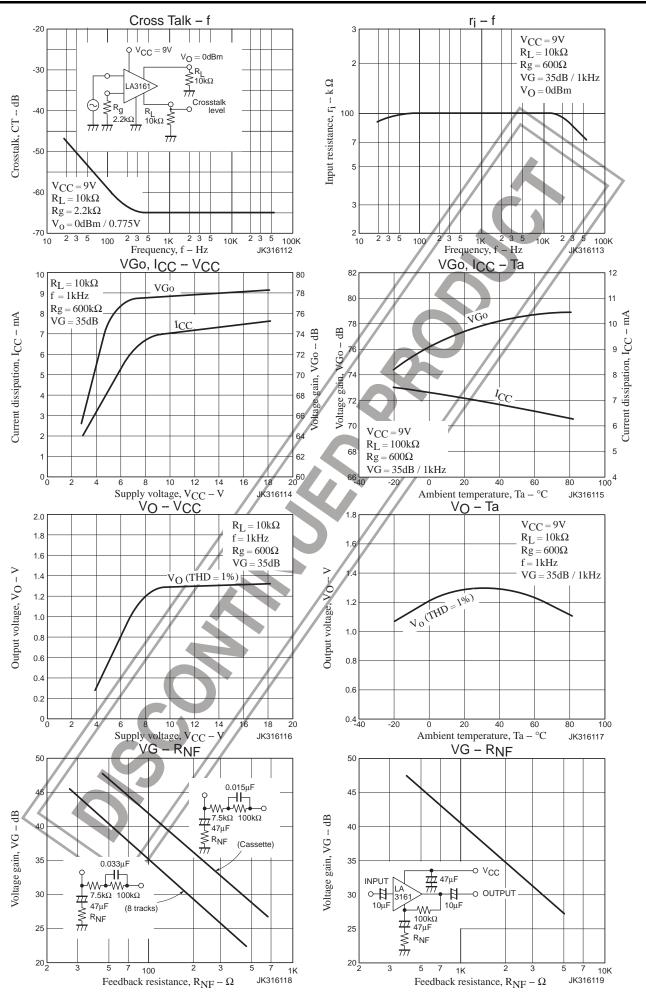
3. Breakdown of IC attributable to inverted insertion

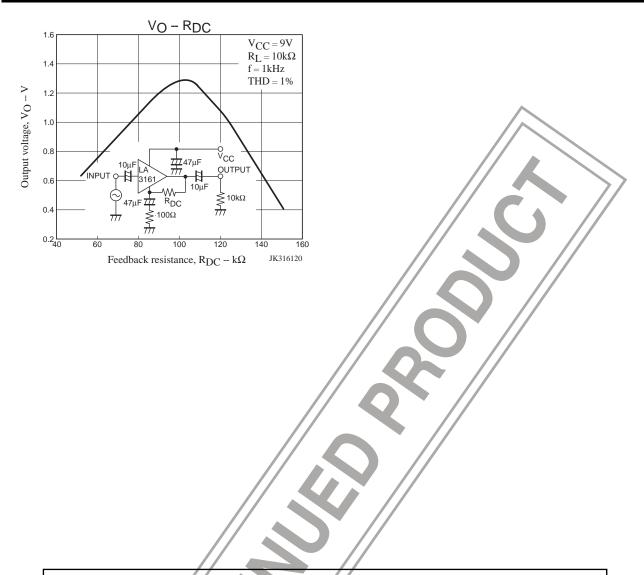
If the IC is inserted inversely and operated, the IC may suffer from something unusual, thereby leading to a breakdown or deterioration of the IC. When installing the IC on the board or operating the IC, check the marked surface of IC.

Proper cares to be taken for obtaining optimum operation of IC

- Set DC resistance of R1, R2 of NAB element at approximately 100kΩ.
- Determine the gain by changing R_{NF} without chaging NAB constant (Refer to Examples of NAB constant.).







- SANYO Semiconductor Co.,Ltd. assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein.
- SANYO Semiconductor Co.,Ltd. strives to supply high-quality high-reliability products, however, any and all semiconductor products fail or malfunction with some probability. It is possible that these probabilistic failures or malfunction could give rise to accidents or events that could endanger human lives, trouble that could give rise to smoke or fire, or accidents that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO Semiconductor Co.,Ltd. products described or contained herein are controlled under any of applicable local export control laws and regulations, such products may require the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written consent of SANYO Semiconductor Co.,Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor Co.,Ltd. product that you intend to use.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.
- Upon using the technical information or products described herein, neither warranty nor license shall be granted with regard to intellectual property rights or any other rights of SANYO Semiconductor Co.,Ltd. or any third party. SANYO Semiconductor Co.,Ltd. shall not be liable for any claim or suits with regard to a third party's intellctual property rights which has resulted from the use of the technical information and products mentioned above.

This catalog provides information as of April, 2008. Specifications and information herein are subject to change without notice.